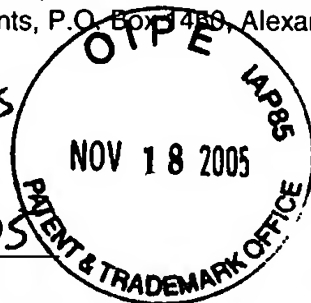


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Robert Faber 11-10-05
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of _____:

Cheng, et al. _____:

Group Art Unit: 2822

Serial No: 10/605,227 _____:

Examiner: Kiesha L. Rose

Filed: 9/16/03 _____:

International Business Machines Corporation
2070 Route 52
Hopewell Junction, NY 12533

TITLE: STRUCTURE OF VERTICAL STRAINED SILICON DEVICES

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the US and non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,
Cheng, et al.

By _____

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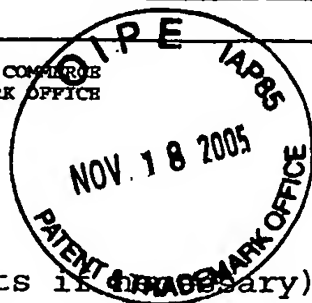
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Atty. Docket No.

FIS920030221US1

Serial No.

10/605,227

Applicants

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Filing Date

9/16/03

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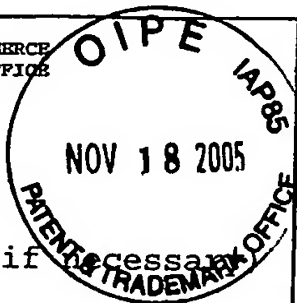
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